



12V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	$11m\Omega @ V_{GS} = -4.5V$	-11A
-12V	$14m\Omega @ V_{GS} = -3.7V$	-9.7A
	$19m\Omega @ V_{GS} = -2.5V$	-8.3A
	$30m\Omega$ @ $V_{GS} = -1.8V$	-6.6A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

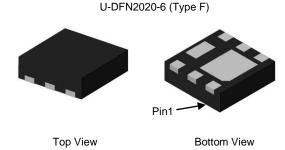
- **Battery Management Application**
- **Power Management Functions**
- DC-DC Converters

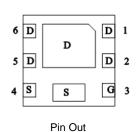
Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low On-Resistance
- Fast Switching Speed
- 100% Unclamped Inductive Switching (Test in Production) -**Ensures More Reliability**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

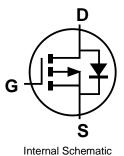
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.007 grams (Approximate)





Bottom View



Ordering Information (Note 5)

Part Number	Case	Packaging
DMP1009UFDFQ-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMP1009UFDFQ-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



FZ = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019)M = Month (ex: 9 = September)

Date Code Key

Year	2017		2018	2019		2020	2021		2022	2023		2024
Code	Е		F	G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-12	V		
Gate-Source Voltage			V_{GSS}	±8	V
	1	-11	^		
Continuous Dusin Comment V 4 5V (Nate 7)	Steady State	T _A = +70°C	I _D	-8.7	A
Continuous Drain Current $V_{GS} = -4.5V$ (Note 7)	t<5s	T _A = +25°C	· I _D	-15	А
		T _A = +70°C		-12	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-70	Α	
Maximum Body Diode Continuous Current (Note 7)	Is	-2.5	Α		
Avalanche Current (Note 8) L = 0.1mH	I _{AS}	-24	Α		
Avalanche Energy (Note 8) L = 0.1mH	E _{AS}	31	mJ		

Thermal Characteristics

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	0.8	W	
Thermal Begistenes, Junction to Ambient (Note 6)	Steady State	<u> </u>	152	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	t<5s R _{θJA}		C/VV	
Total Power Dissipation (Note 7)	$T_A = +25^{\circ}C$	P_{D}	2.0	W	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	<u> </u>	63	°C/W	
Thermal Resistance, Junction to Ambient (Note 7)	t<5s	$R_{\theta JA}$	34		
Thermal Resistance, Junction to Case (Note 7)	Steady State	$R_{\theta JC}$	15		
Operating and Storage Temperature Range		T _{J.} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}		_	-100	nA	$V_{DS} = -9.6V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	1	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.3	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			8.3	11		$V_{GS} = -4.5V$, $I_{D} = -5A$
Static Drain-Source On-Resistance	Ь		9	14	mΩ	$V_{GS} = -3.7V, I_D = -5A$
Static Dialif-Source Off-Resistance	R _{DS(ON)}	_	12	19	11177	$V_{GS} = -2.5V, I_{D} = -4A$
			16	30		$V_{GS} = -1.8V, I_{D} = -1A$
Diode Forward Voltage	V_{SD}		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -10A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}		1860			V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	Coss	_	498	_	pF	
Reverse Transfer Capacitance	C _{rss}	_	416	_		1 - 1.000112
Gate Resistance	R_g	_	11	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	26	_		
Total Gate Charge (V _{GS} = -8V)	Qg	_	44	_	nC	
Gate-Source Charge	Q_{gs}	_	3.3	_	IIC	$V_{DS} = -6V, I_{D} = -10A$
Gate-Drain Charge	Q_{gd}	_	8.1	_		
Turn-On Delay Time	t _{D(ON)}	_	7.0	_		
Turn-On Rise Time	t _R	_	10.6	_		$V_{DS} = -6V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	62.2	_	ns	$R_g = 1\Omega$, $I_D = -8A$
Turn-Off Fall Time	t _F	_	61	_		
Reverse Recovery Time	t _{RR}	_	34.4	_	ns	1 400 11/14 5000/
Reverse Recovery Charge	Q_{RR}	_	28.1	_	nC	$I_F = -12A$, di/dt = 500A/ μ s

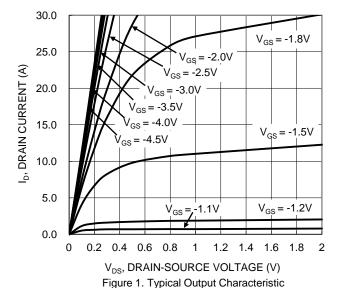
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.





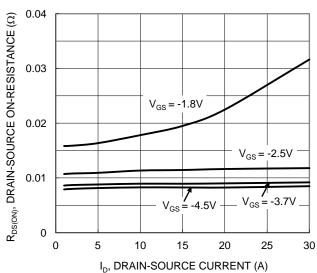


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

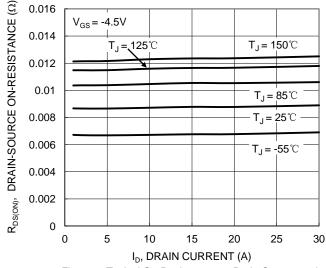


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

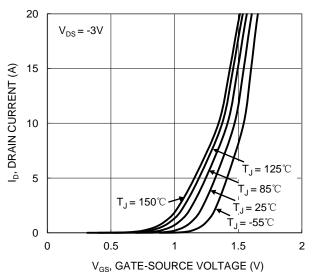


Figure 2. Typical Transfer Characteristic

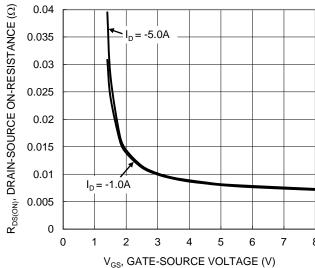


Figure 4. Typical Transfer Characteristic

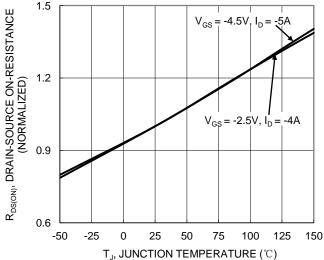


Figure 6. On-Resistance Variation with Temperature



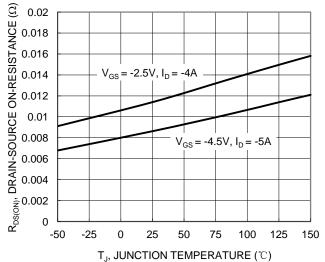
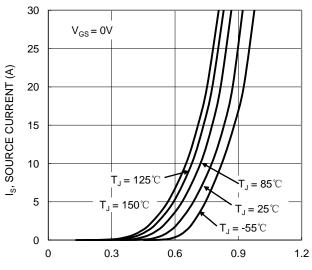
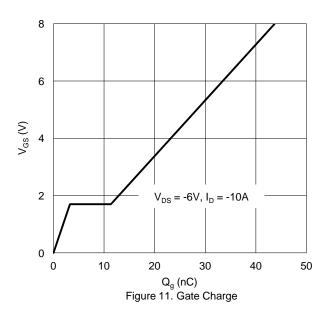


Figure 7. On-Resistance Variation with Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



 T_J , JUNCTION TEMPERATURE ($^{\circ}$ C) Figure 8. Gate Threshold Variation vs. Junciton Temperature

50

75

100

125

150

25

-50

-25

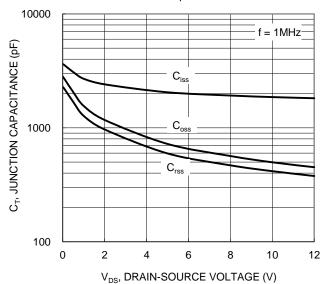
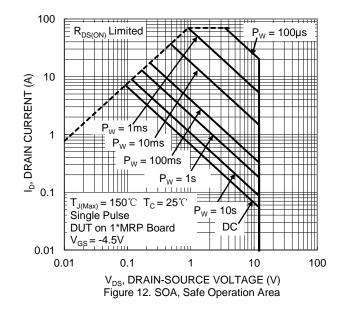


Figure 10. Typical Junction Capacitance





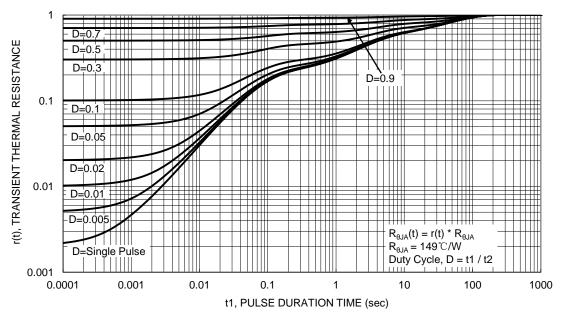


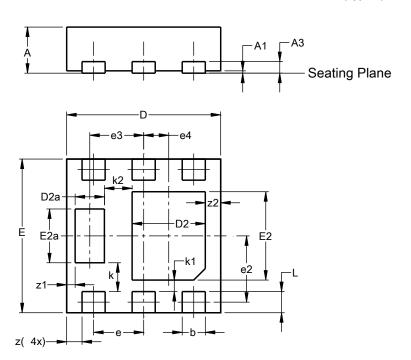
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

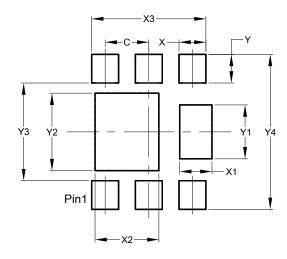


U-DFN2020-6								
(Type F)								
Dim	Min	Max	Тур					
Α	0.57	0.63	0.60					
A1	0.00	0.00 0.05 0.03						
A3	-	-	0.15					
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
D2a	0.33	0.43	0.38					
Е	1.95	2.05	2.00					
E2	1.05							
E2a	0.65	0.75	0.70					
е	0.65 BSC							
e2	(0.863 BSC						
е3		0.70 BS	C					
e4	(0.325 BSC						
k		0.37 BS	С					
k1	0.15 BSC							
k2	0.36 BSC							
L	0.225 0.325 0.275							
Z	0.20 BSC							
z 1	0.110 BSC							
z2	0.20 BSC							
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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7 of 7 DMP1009UFDFQ May 2019 Datasheet number: DS41367 Rev. 2 - 2

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